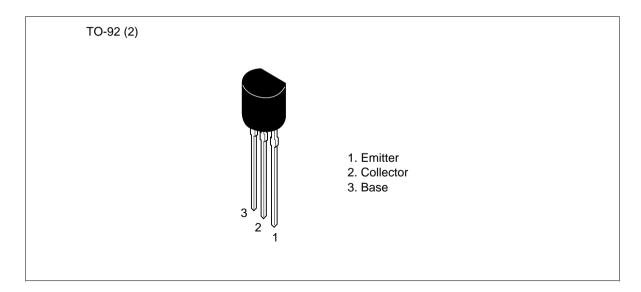
Silicon NPN Epitaxial Planar

HITACHI

Application

- VHF amplifier, mixer
- Local oscollator

Outline





Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

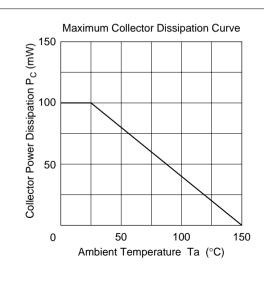
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	30	V
Collector to emitter voltage	V_{CEO}	20	V
Emitter to base voltage	V_{EBO}	4	V
Collector current	I _c	30	mA
Collector power dissipation	P _c	100	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

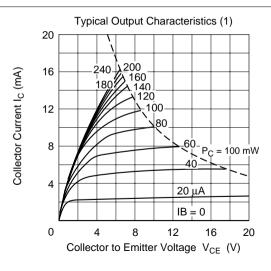
Electrical Characteristics (Ta = 25°C)

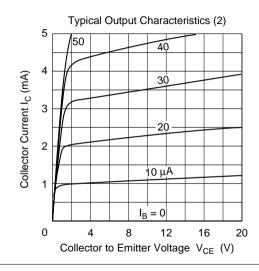
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	30	_	_	V	$I_{c} = 10 \ \mu\text{A}, \ I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	20	_	_	V	I_{c} = 1 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	4	_	_	V	$I_{E} = 10 \ \mu A, \ I_{C} = 0$
Collector cutoff current	I _{CBO}	_	_	0.5	μΑ	$V_{CB} = 10 \text{ V}, I_{E} = 0$
DC current transfer ratio	h _{FE} *1	35	_	200		$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	_	0.8	1.2	V	$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 1 mA
Collector output capacitance	Cob	_	1.1	1.5	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$
Base time constant	r _{bb′} ∙C _C	_	20	35	ps	$V_{CB} = 6 \text{ V}, I_{C} = 1 \text{ mA},$ f = 31.8 MHz
Gain bandwidth product	f _T	150	320	_	MHz	$V_{CE} = 6 \text{ V}, I_{C} = 1 \text{ mA}$
Noise figure	NF	_	5.5	8.5	dB	V_{CE} = 6 V, I_{C} = 1 mA, f = 100 MHz, R_{g} = 50 Ω
Reverse transfer capacitance	Cre	_	0.9	1.2	pF	$V_{CE} = 10 \text{ V}, I_{E} = -1 \text{ mA},$ f = 1 MHz
Power gain	PG	13	17	_	dB	V_{CE} = 6 V, I_{C} = 1 mA, f = 100 MHz, R_{g} = 100 Ω , R_{L} = 550 Ω , Unneutralized

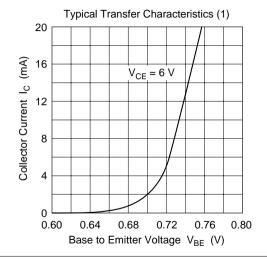
Note: 1. The 2SC1342 is grouped by $h_{\rm FE}$ as follows.

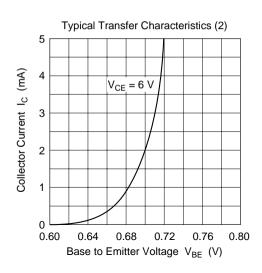
Α	В	С
35 to 70	60 to 120	100 to 200

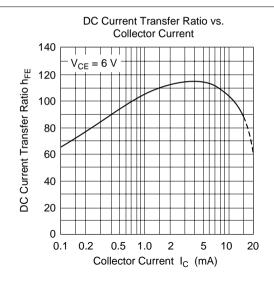


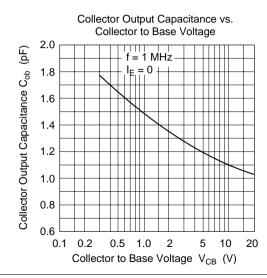


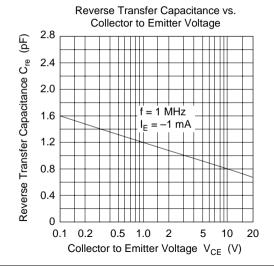


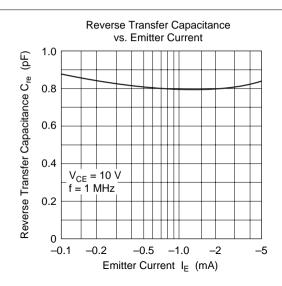


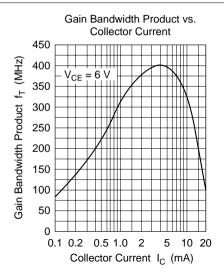


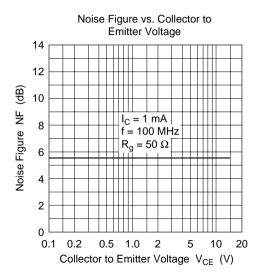


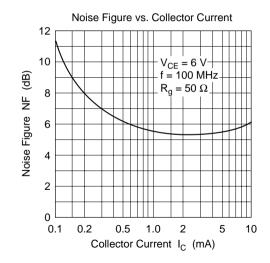




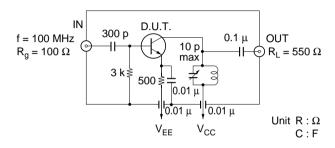






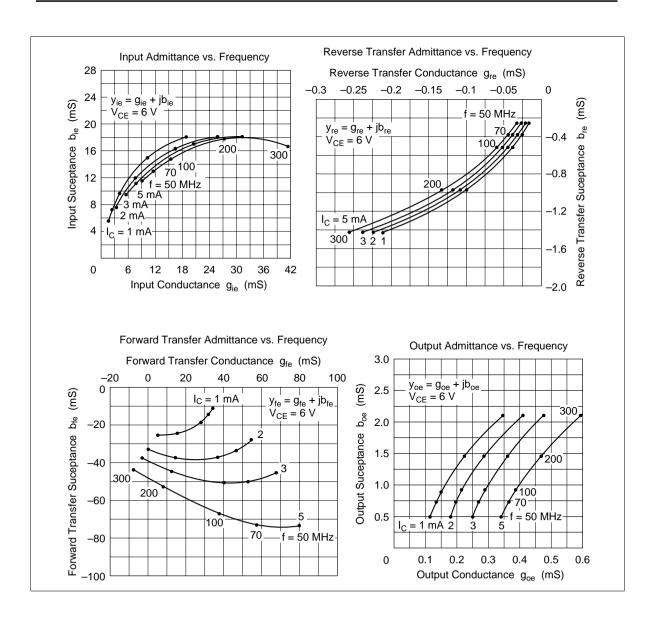


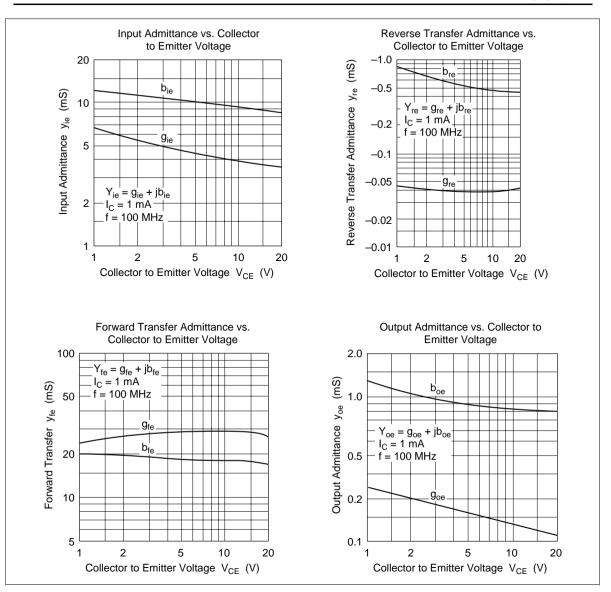
Power Gain Test Circuit

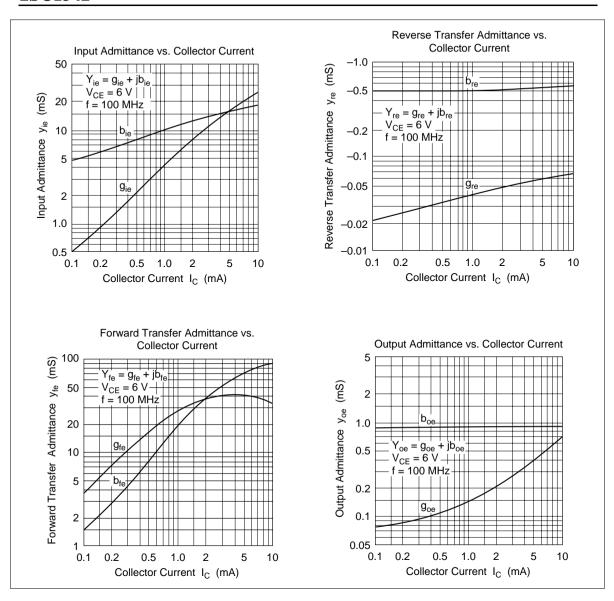


Small Signal y Parameters ($V_{CE} = 6V$, $I_C = 1$ mA, Emitter Common Ta = 25°C)

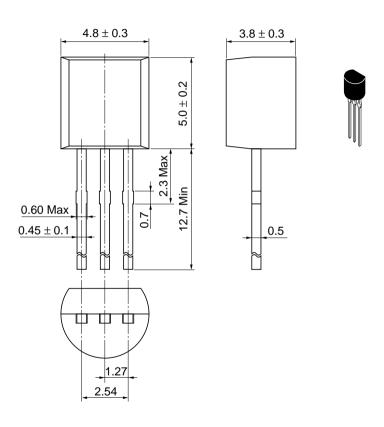
Item	Symbol	f = 50 MHz	f = 100 MHz	f = 200 MHz	Unit
Input admittance	yie	1.8 + j5.5	4.3 + j9.9	11.5 + j15.25	mS
Reverse transfer admittance	yre	-0.022 - j0.26	-0.04 - j0.52	-0.105 - j0.96	
Forward transfer admittance	yfe	34 – j12	28 – j19	15.5 – j25	_
Output admittance	yoe	0.1 + j0.5	0.15 + j0.9	0.21 + j1.45	_







Unit: mm



Hitachi Code	TO-92 (2)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

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